

Pulsed CVD of amorphous GeSe for application as OTS selector  
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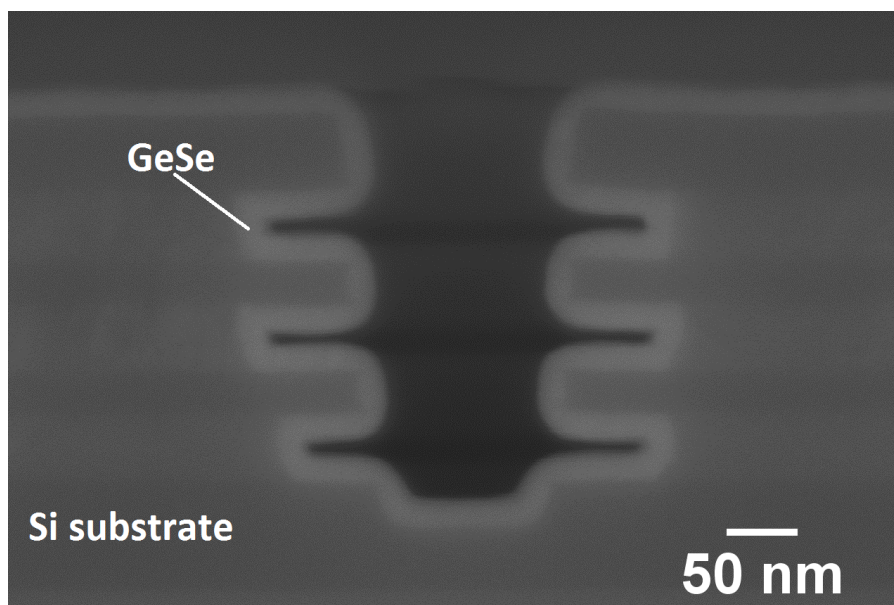


Figure 1. Conformally grown pulsed CVD GeSe on 3D test structure

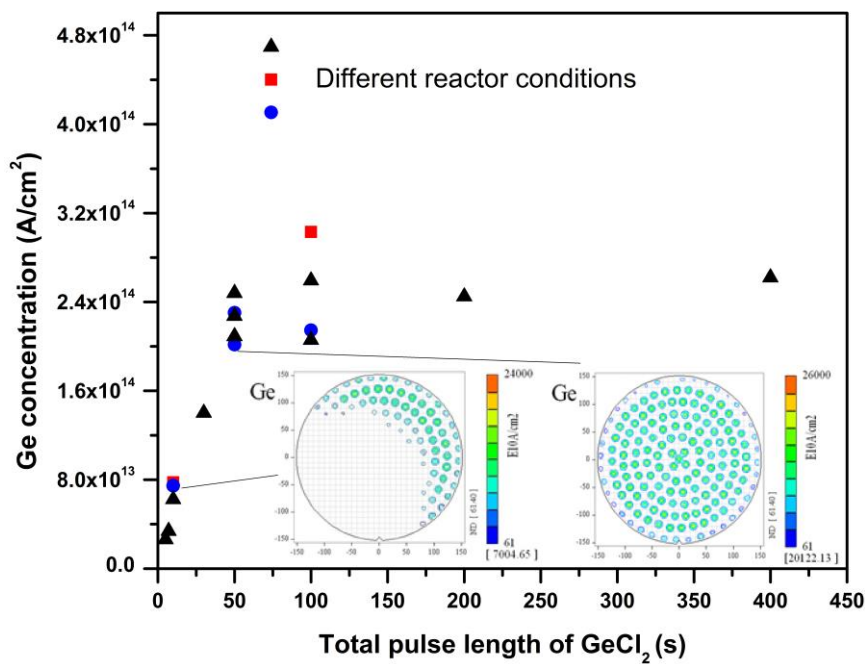


Figure 2. Ge chemisorption on SiO<sub>x</sub> is slow (TXRF measurements), limited by precursor supply/slower injection